LSIC2SD065C16A 650 V, 16 A SiC Schottky Barrier Diode









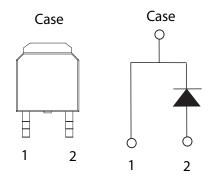
Description

This series of silicon carbide (SiC) Schottky diodes has negligible reverse recovery current, high surge capability, and a maximum operating junction temperature of 175 °C. These diodes series are ideal for applications where improvements in efficiency, reliability, and thermal management are desired.

Features

- AEC-Q101 qualified
- Positive temperature coefficient for safe operation and ease of paralleling
- 175 °C maximum operating junction temperature
- Excellent surge capability
- Extremely fast, temperature-independent switching behavior
- Dramatically reduced switching losses compared to Si bipolar diodes

Circuit Diagram TO-252-2L (DPAK)



Applications

- Boost diodes in PFC or DC/DC stages
- Switch-mode power supplies
- Uninterruptible power supplies
- · Solar inverters
- Industrial motor drives
- EV charging stations

Environmental

- Littelfuse "RoHS" logo = RoHS RoHS conform
- Littelfuse "HF" logo = HF Halogen Free
- Littelfuse "Pb-free" logo = Pb-free lead plating

=	P 0

Maximum Ratings						
Characteristics	Symbol	Conditions	Value	Unit		
Repetitive Peak Reverse Voltage	V _{RRM}	-	650	V		
DC Blocking Voltage	V _R	T _J = 25 °C	650	V		
		T _C = 25 °C	38	А		
Continuous Forward Current	l _F	T _C = 135 °C	17.2			
		T _C = 140 °C	16			
Non-Repetitive Forward Surge Current	I _{FSM}	$T_{\rm C} = 25 {\rm ^{\circ}C}$, $T_{\rm P} = 10 {\rm ms}$, Half sine pulse	70	А		
Power Dissipation	В	T _C = 25 °C	125	W		
rowel Dissipation	P _{Tot}	T _C = 110 °C	T _c = 110 °C 54			
Operating Junction Temperature	T	-	-55 to 175	°C		
Storage Temperature	T _{STG}	-	-55 to 150	°C		
Soldering Temperature (reflow MSL1)	T _{sold}	-	260	°C		

Electrical Characteristics

		Symbol Conditions	Value			
Characteristics	Symbol		Min.	Тур.	Max.	Unit
Forward Voltage	V _F	I _F = 16 A, T _J = 25 °C	-	1.5	1.8	V
		I _F = 16 A, T _J = 175 °C	-	1.85	-	
Reverse Current		$V_R = 650 \text{V}$, $T_J = 25 ^{\circ}\text{C}$	-	<1	50	μА
	I _R	$V_{R} = 650 \text{V}$, $T_{J} = 175 ^{\circ}\text{C}$	-	55	-	
Total Capacitance		$V_R = 1 V$, $f = 1 MHz$	-	730	-	
	С	$V_R = 200 \text{ V, f} = 1 \text{ MHz}$	-	92	-	pF
		$V_R = 400 \text{V}, \text{f} = 1 \text{MHz}$	-	66	-	
Total Capacitive Charge	Q _c	$V_R = 400 \text{ V}, \ \ Q_C = \int\limits_0^{V_R} c(V) dV$	-	48	-	nC

Footnote: $T_J = +25$ °C unless otherwise specified

Thermal Characteristics						
Characteristics	Symbol	Value	Unit			
Thermal Resistance	R	1.2	°C/W			

Figure 1: Typical Foward Characteristics

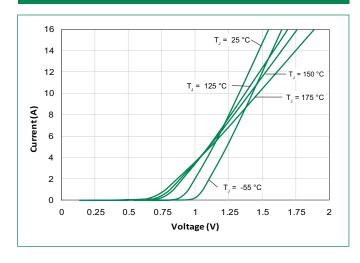


Figure 2: Typical Reverse Characteristics

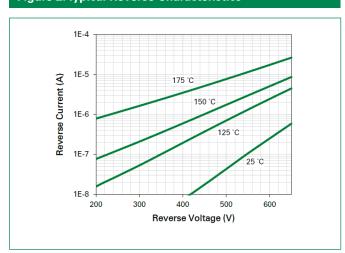




Figure 3: Power Derating

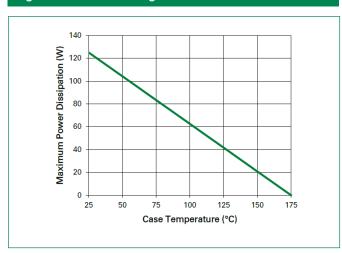


Figure 4: Current Derating

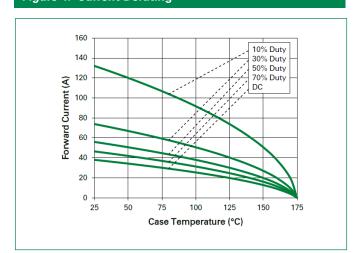


Figure 5: Capacitance vs. Reverse Voltage

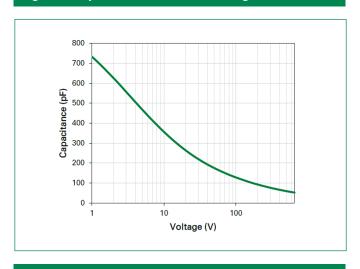


Figure 6: Capacitive Charge vs. Reverse Voltage

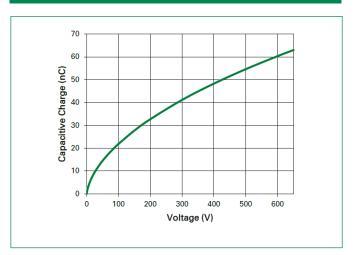


Figure 7: Stored Energy vs. Reverse Voltage

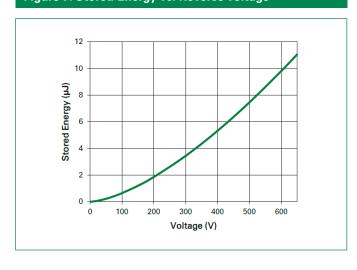
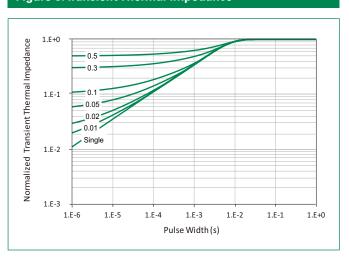
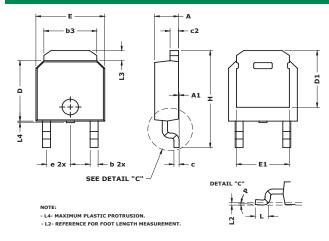


Figure 8: Transient Thermal Impedance

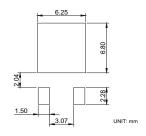




Dimensions TO-252-2L (DPAK)

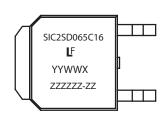


Recommended Solder Pattern Layout



Symbol	Inches			Millimeters		
Зутпрог	Min	Nom	Max	Min	Nom	Max
Α	0.085	0.090	0.095	2.16	2.29	2.41
A1	0	0.003	0.005	0	0.08	0.13
b	0.025	0.030	0.035	0.64	0.76	0.89
b3	0.195	0.200	0.215	4.95	5.08	5.46
С	0.018	0.020	0.024	0.46	0.51	0.61
C2	0.018	0.032	0.035	0.46	0.81	0.89
D	0.235	0.240	0.245	5.97	6.10	6.22
D1	0.205	-	-	5.21	-	-
Е	0.250	0.260	0.265	6.35	6.60	6.73
E1	0.170	-	-	4.32	-	-
е	0.090 BSC			2.29 BSC		
Н	0.370	0.387	0.410	9.40	9.83	10.41
L	0.040	0.045	0.050	1.02	1.14	1.27
L2	0.010 BSC			0.25 BSC		
L3	0.035	-	0.050	0.89	-	1.27
L4	0	-	0.006	0	-	0.15
Р	0°	-	8°	0°	-	8°

Part Numbering and Marking System



SIC	= SiC Diode
2	= Gen2
SD	= Schottky Diode
065	= Voltage Rating (650 V
С	= TO-252-2L (DPAK)
16	= Current Rating (16 A)
YY	= Year
WW	= Week

= Special code

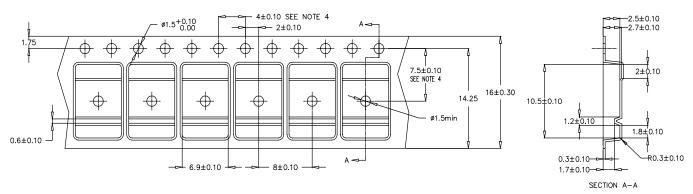
X = Special code ZZZZZZ-ZZ = Lot Number

Packing Options

Part Number Marking		Packing Mode	M.O.Q
LSIC2SD065C16A	SIC2SD065C16	Tape and Reel	2500

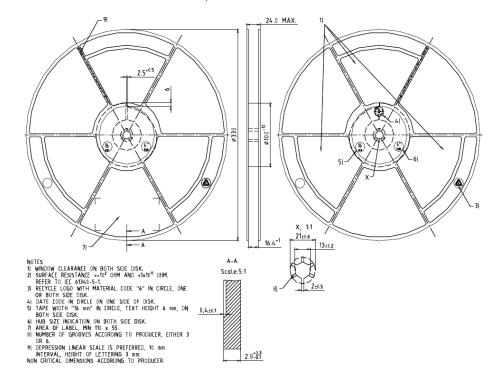


Carrier Tape & Reel Specification TO-252-2L (DPAK)



- Material: Black Conductive Polysterene

- 1. Material: Black Conductive Polysterene
 2. 10 sprocket hole pitch cumulative tolerance ± 0.20
 3. Camber not to exceed 1 mm in 100 mm.
 4. Pocket position relative to sprocket hole measured as true position of pocket, not pocket hole.
 5. Device orientation: TRL (leads perpendicular to the sprocket)
- General tolerance is \pm 0.10 mm unless otherwise specified.



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